

Attorney's Docket No.: 14580-031001

Amendments to the Specification:

Please replace the paragraph beginning at page 3, line 22 with the following amended paragraph:

Specifically, ~~a first expression~~ one embodiment of the invention is a method of forming a ferroelectric capacitor comprising forming a crystalline PZT layer by a process including the steps of:

depositing a layer of amorphous ferroelectric material over a layer of a first material;

etching the ferroelectric layer to form isolated ferroelectric elements;

providing a layer of a second material on at least the side surfaces of the ferroelectric elements; and

performing an annealing step to crystallize the ferroelectric material;

the second material promoting crystallisation of the ferroelectric material to a higher degree than the first material, whereby the crystallisation proceeds horizontally through the ferroelectric elements.

Another embodiment of the invention is method of forming a vertical ferromagnetic capacitor comprising forming a crystalline ferroelectric layer by a process including the steps of:

depositing a ferroelectric layer of amorphous ferroelectric material directly on a layer of a first electrically insulating material;

depositing a layer of a second electrically insulating material to cover the ferroelectric layer;

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etching the ferroelectric layer and the layer of the second electrically insulating material to form isolated ferroelectric elements which have exposed side surfaces;

providing a layer of a conductive material in contact with each of the side surfaces; and

performing an annealing step to crystallize the ferroelectric material;

the conductive material promoting crystallization of the ferroelectric material to a higher degree than the first and second electrically insulating materials, whereby the crystallization proceeds substantially horizontally through each of the ferroelectric elements.